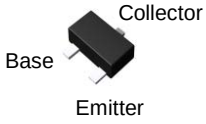
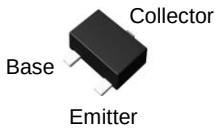
2SCR502EB / 2SCR502UB

NPN 500mA 30V General Purpose Transistors

Datasheet

Parameter	Value
V_{CEO}	30V
I_C	500mA

●Outline

EMT3F	UMT3F
	
2SCR502EB (SC-89)	2SCR502UB (SC-85)

●Features

1)General Purpose.

2) Complementary PNP Types :

2SAR502EB (EMT3F) / 2SAR502UB (UMT3F)

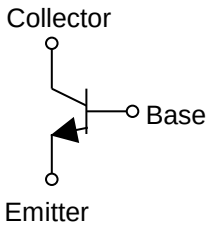
3) Large collector current :

Ic=max.500mA

4) Low $V_{CE(sat)}$

5) Lead Free/RoHS Compliant.

●Inner circuit



●Applications

Switching circuit, LED driver circuit

●Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SCR502EB	EMT3F	1616	TL	180	8	3,000	LW
2SCR502UB	UMT3F	2021	TL	180	8	3,000	LW

●**Absolute maximum ratings** (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V_{CBO}	30	V
Collector-emitter voltage		V_{CEO}	30	V
Emitter-base voltage		V_{EBO}	6	V
Collector current		I_C *1	500	mA
Power dissipation	2SCR502EB	P_D *2	150	mW
	2SCR502UB		200	mW
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	−55 to +150	°C

*1 Limited by power dissipation

*2 Each terminal mounted on a reference land

●**Electrical characteristics**(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage	BV_{CEO}	I_C = 1mA	30	-	-	V
Collector-base breakdown voltage	BV_{CBO}	I_C = 100μA	30	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I_E = 100μA	6	-	-	V
Collector cut-off current	I_{CBO}	V_{CB} = 25V	-	-	200	nA
Emitter cut-off current	I_{EBO}	V_{EB} = 4V	-	-	200	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 200mA, I_B =10mA	-	0.10	0.30	V
DC current gain	h_{FE} *3	V_{CE} = 2V, I_C = 100mA	200	-	500	-
Transition frequency	f_T *3	V_{CE} = 10V, I_E = −100mA f=100MHz	-	360	-	MHz
Output capacitance	Cob	V_{CB} = 10V, I_E = 0A, f = 1MHz	-	3.0	-	pF

*3 Pulsed

●**Electrical characteristic curves**(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

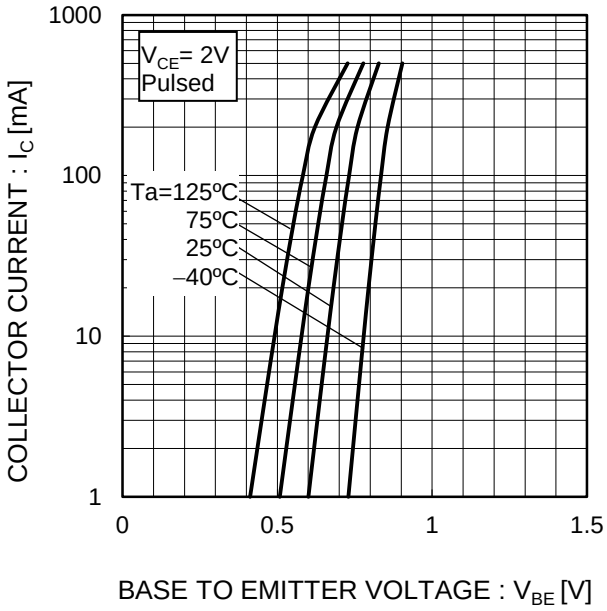


Fig.2 Typical Output Characteristics

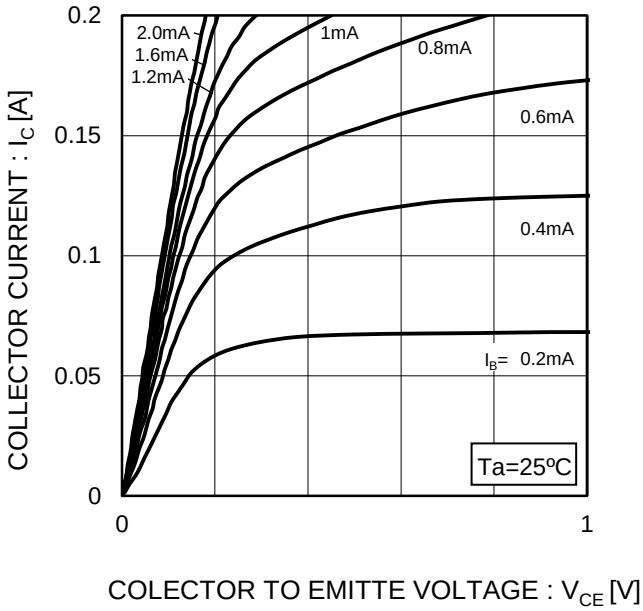


Fig.3 DC Current Gain vs. Collector Current(I)

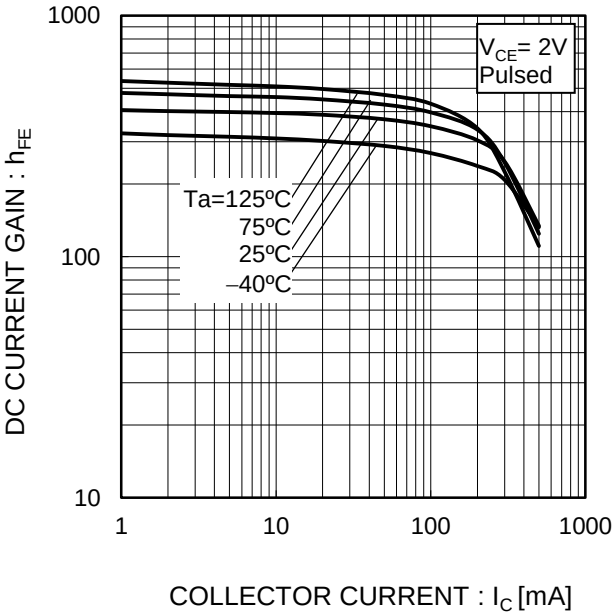
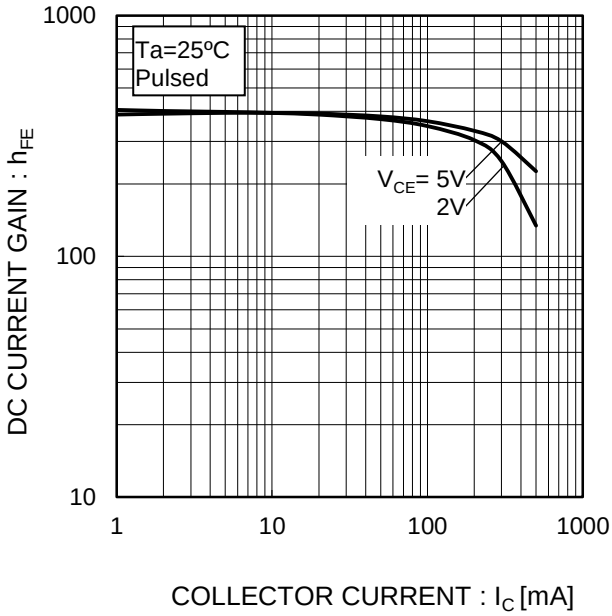


Fig.4 DC Current Gain vs. Collector Current(II)



●**Electrical characteristic curves**(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

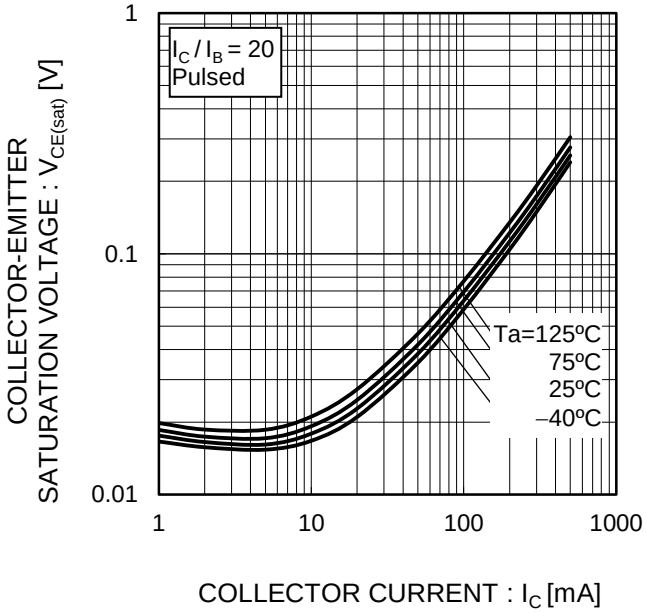


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

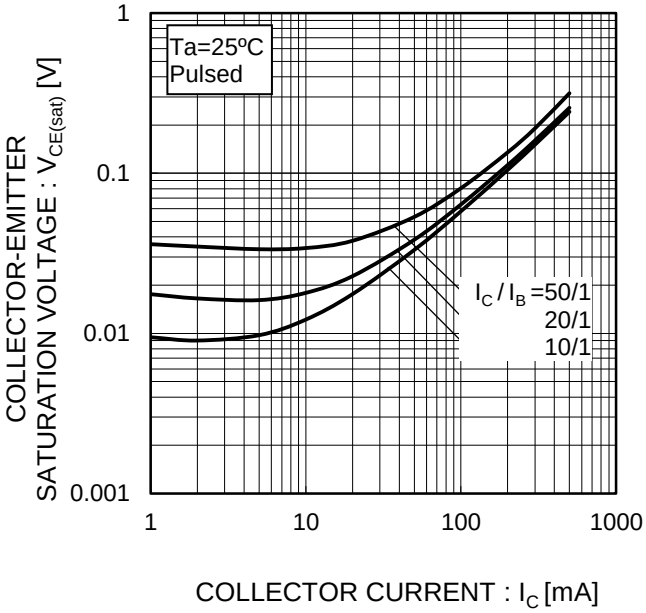


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

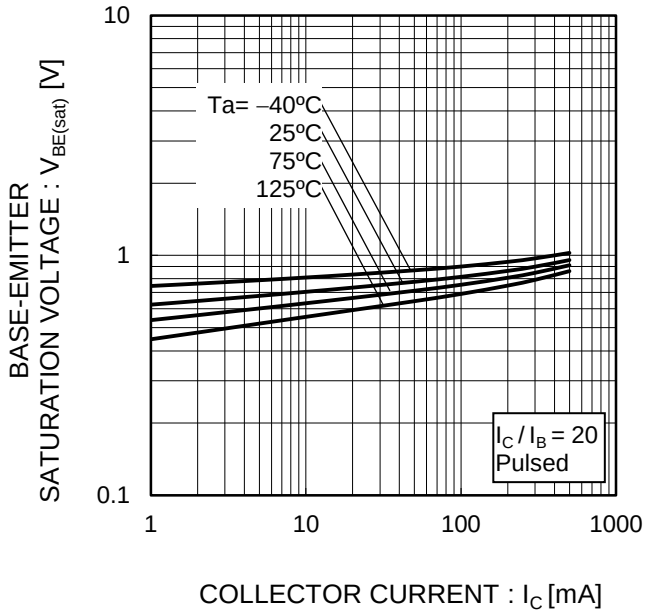
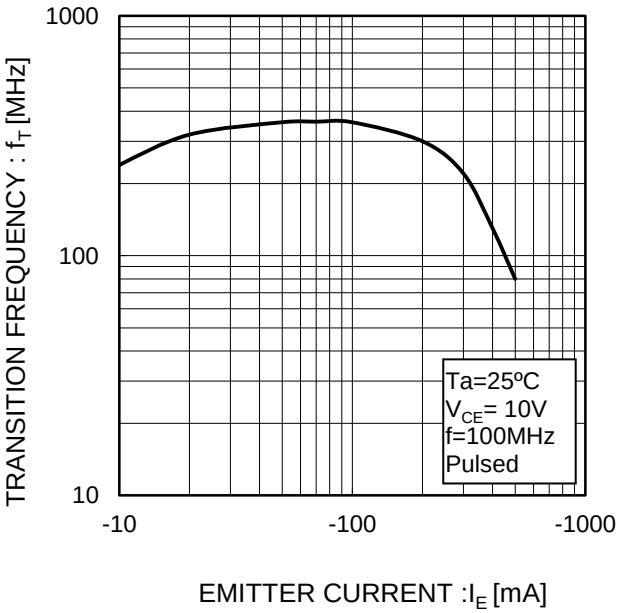


Fig.8 Gain Bandwidth Product vs. Emitter Current



●**Electrical characteristic curves**(Ta = 25°C)

Fig.9 Emitter input capacitance vs. Emitter-Base Voltage
Collector output capacitance vs. Collector-Base Voltage

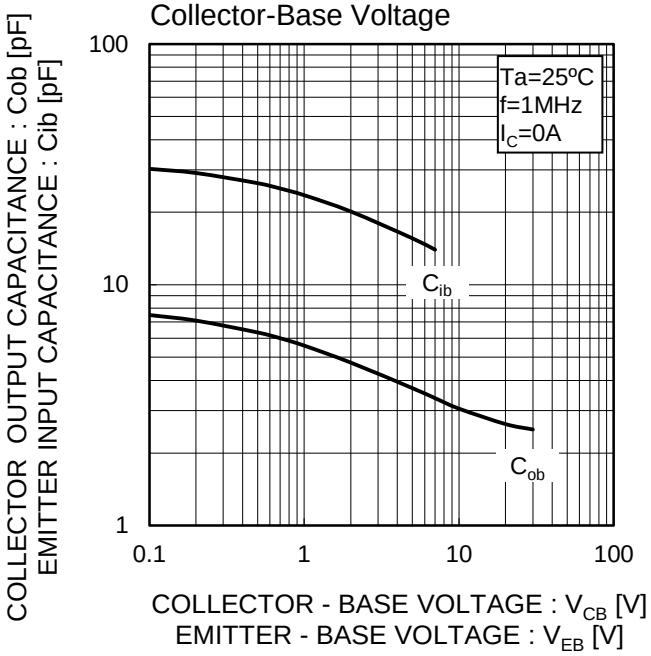


Fig.10 Safe Operating Area

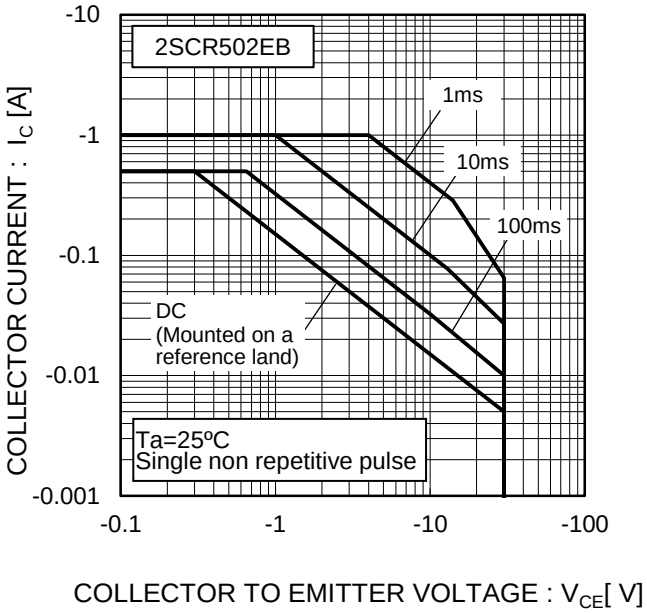
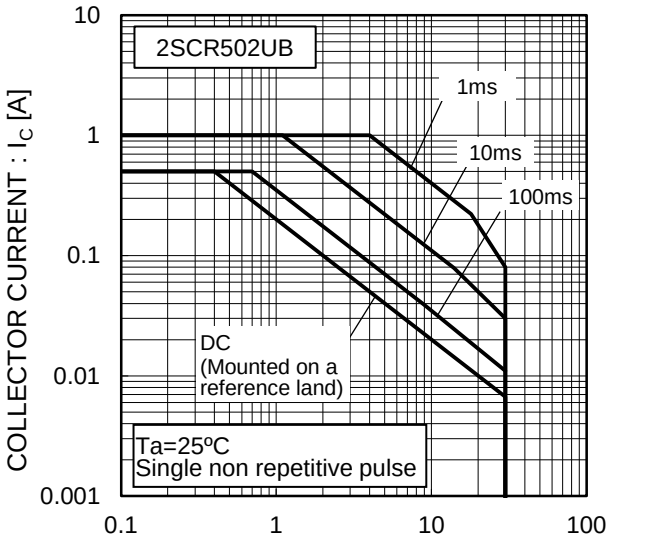
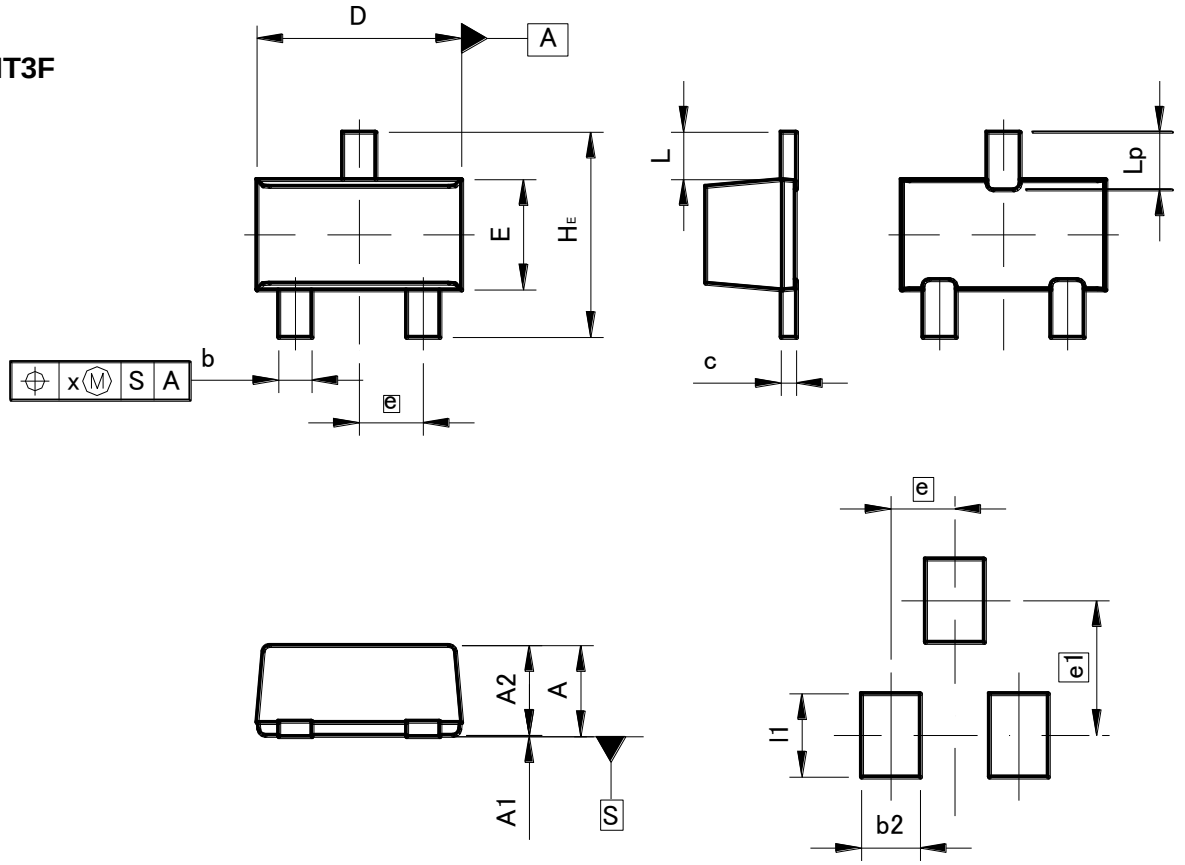


Fig.11 Safe Operating Area



●**Dimensions** (Unit : mm)

EMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

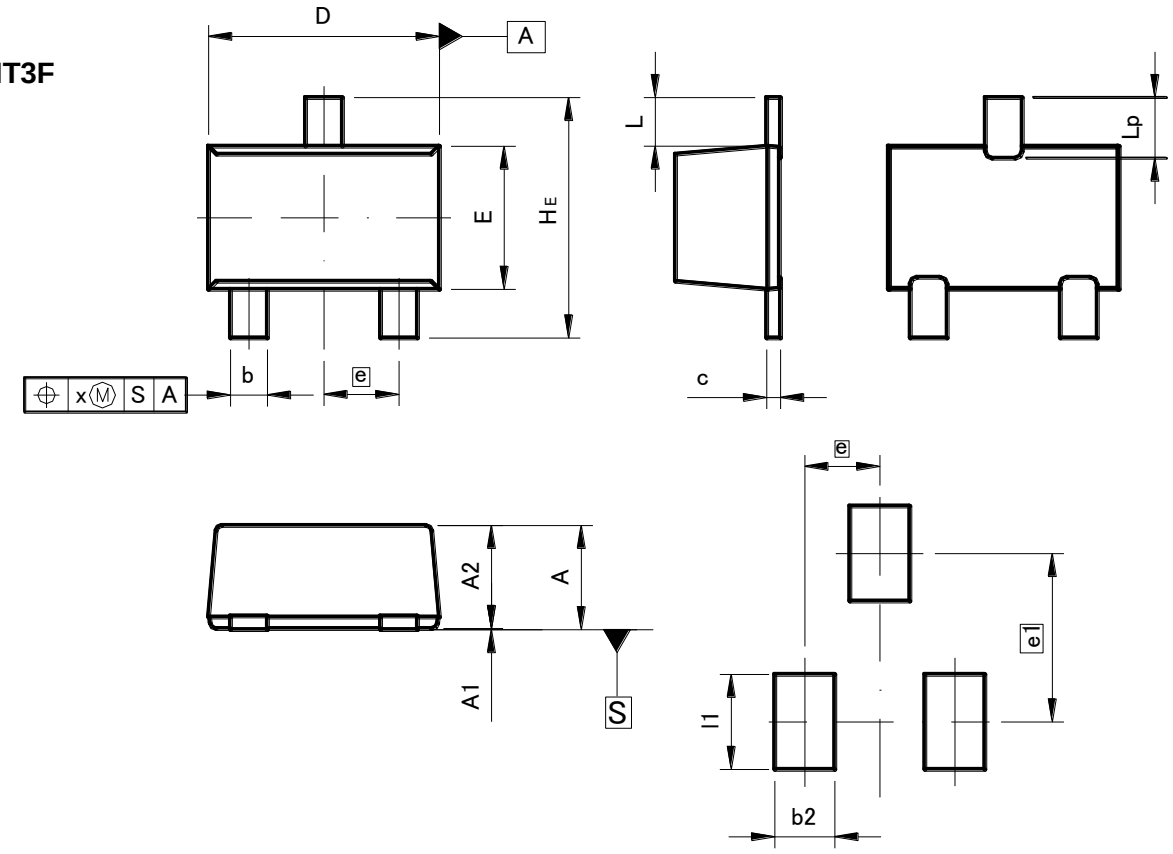
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.46	−	0.018
e1	−	1.05	−	0.041
l1	−	0.65	−	0.026

Dimension in mm / inches

●**Dimensions** (Unit : mm)

UMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
c	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L	0.43		0.017	
Lp	0.43	0.63	0.017	0.025
x	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.52	−	0.020
e1	1.47		0.058	
l1	−	0.83	−	0.033

Dimension in mm / inches

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.

6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.

7) The Products specified in this document are not designed to be radiation tolerant.

8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.

9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.

10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.

11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.

12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.

13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.

14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.

ROHM SEMICONDUCTOR

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/